

CHARACTERISATION OF THE ITS3 ANALOGUE PIXEL TEST STRUCTURES PRODUCED IN THE 65 nm TPSCo PROCESS

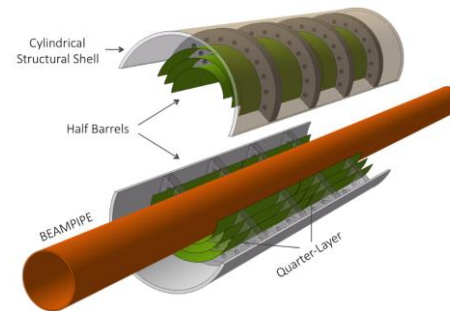
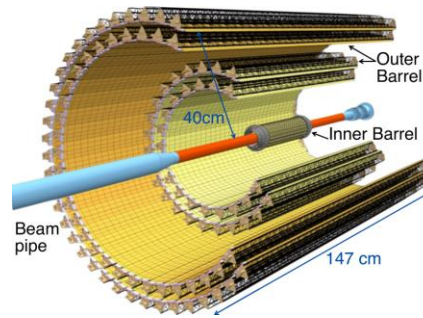
Rebekka Wittwer on behalf of **ALICE**

19th TREDI Workshop on Advanced Silicon Radiation Detectors

ALICE Inner Tracking System

ITS2

- **Largest pixel detector in high energy physics**
- 7 Layers
- 10 m² active area
- 24k 180 nm CMOS MAPS
- 12.5 GPixel **ALPIDE** chip
- Stable, > **99 % functional**
- Material budget: **0.35 % X/X₀**
- Beam pipe radius: 18.2 mm
- Radial position: 24 mm
- Water cooling



ITS3

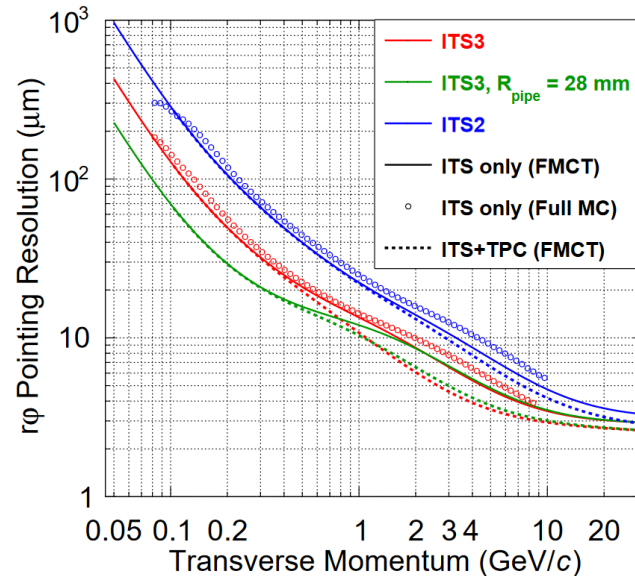
- Replace three innermost layers of ITS2
- **Ultra thin (50μm) and bendable** → half-cylindrical detection layers with self-supported arched structure
- Commercial **65 nm CMOS** imaging technology and stitching
- Material budget: **0.05 % X/X₀**
- Beam pipe radius: 16 mm
- Radial position: 18 mm
- Air cooling

ALICE Inner Tracking System

ITS2

- Largest pixel detector in energy physics
- 7 Layers
- 10 m² active area
- 24k 180 nm CMOS MAPS
- 12.5 GPixel **ALPIDE** chip
- Stable, > 99 % functional
- Material budget: **0.35 % X₀**
- Beam pipe radius: 18.2 mm
- Radial position: 24 mm
- Water cooling

Improvement of factor 2 over all momenta



- Replace three innermost layers
- ITS2
- Thin (50µm) and bendable
- Half-cylindrical detection
- Layers with self-supported arched structure
- Commercial **65 nm CMOS**
- Mapping technology and stitching
- Material budget: **0.05 % X₀**
- Beam pipe radius: 16 mm
- Radial position: 18 mm
- Water cooling

Synergy with Lepton Colliders

How can FCC-ee benefit from ALICE ITS3 developments?

ALICE ITS3 is a stepping stone for lepton colliders with similar requirements:

- Moderate radiation environment
- Low material budget and high spatial resolution is crucial
- First layer closer to the beam pipe for better IP resolution

	ALICE ITS3	FCC-ee
Position Precision	5 μm	3 μm
Low X/X_0	0.05 %	0.3 %
Radiation Tolerance NIEL	$< 10^{13}$	$< 10^{13}$

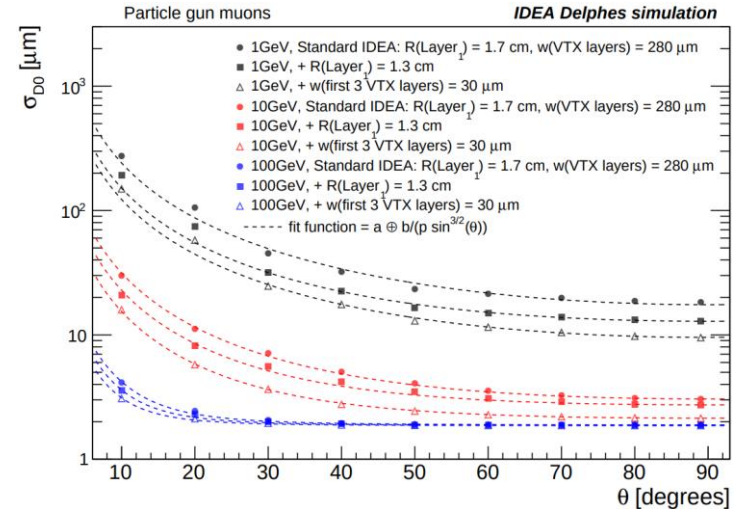
Future collider groups joined the ITS3 efforts:

M. Mager, [FCCW2023](#)

D. Contardo, [FCCW2023](#)

F. Palla, [FCCPW2024](#)

A. Ilg, [FCCPW2024](#)

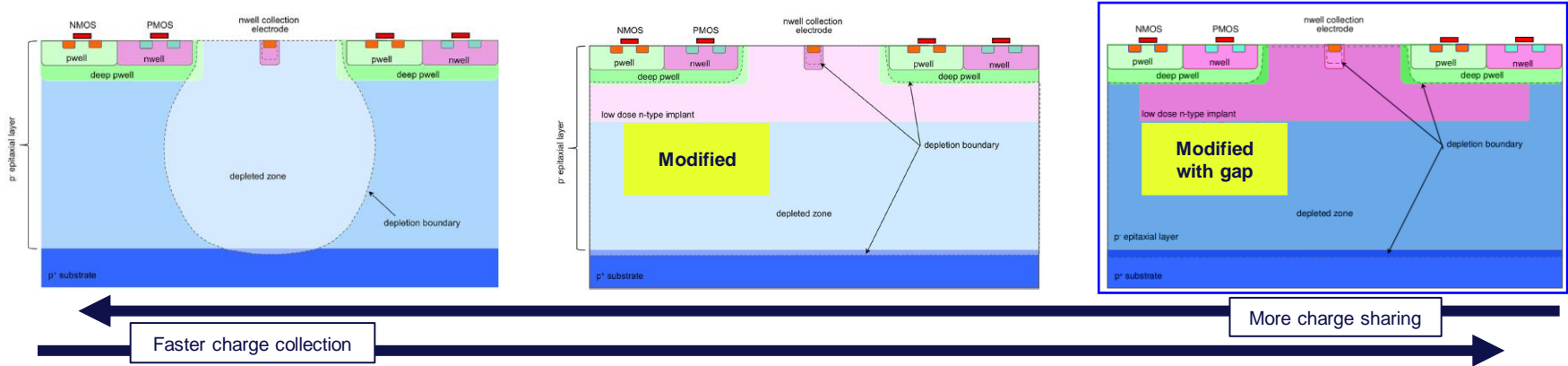


L. Freitag & A. Ilg, [FCCPW](#)

L. Freitag, [Bachelor_Thesis](#)

TPSCo 65 nm Process and Modifications

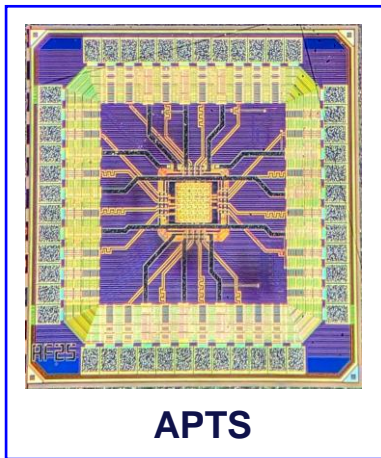
How do we characterise this process?



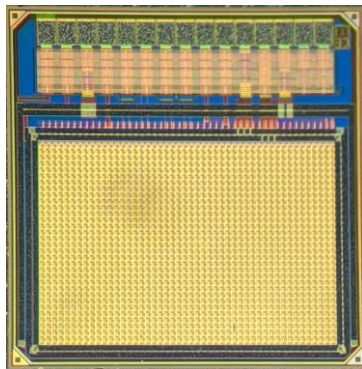
- **Deep p-well** shields the CMOS circuitry from collecting charge
- Low capacitance of the **small collection electrode** results in lower power consumption
- Applying substrate bias increases depletion and improves radiation tolerance

- Further modifications needed for the full depletion of the sensitive layer:
 - **Modified**: to reach full depletion
 - **Modified with gap**: more control over charge sharing

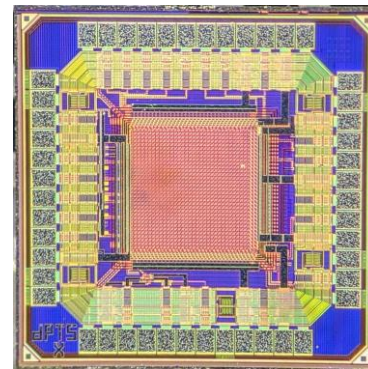
ITS3: Pixel Prototype Chips



- 6x6 pixel matrix
- Direct analog readout of central 4x4 pixels
- Pitch: 10, 15, 20, 25 μm



- 64x64 [v1], 48x32 [v1], 48x24 [v2] pixel matrix
- Rolling shutter analog readout
- Pitch: 15, 25 μm



- 32x32 pixel matrix
- Asynchronous digital readout with ToT
- Pitch: 15 μm

[APTS](#), [CE65](#), [DPTS](#)

Variants of APTS

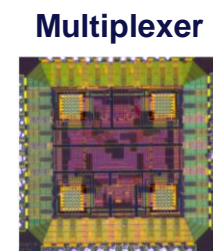
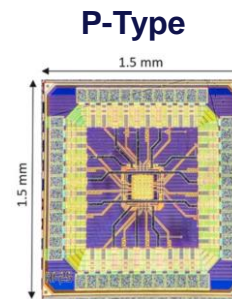
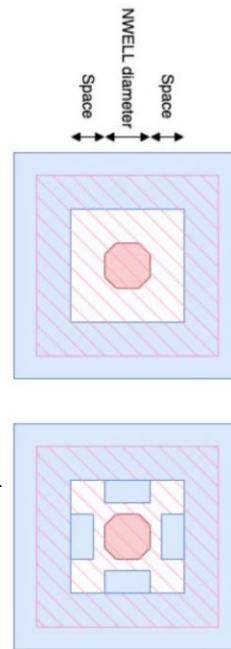
To study the influence on capacitance and charge collection, different variants of the geometry and size of p-well and n-well collection electrode were produced:

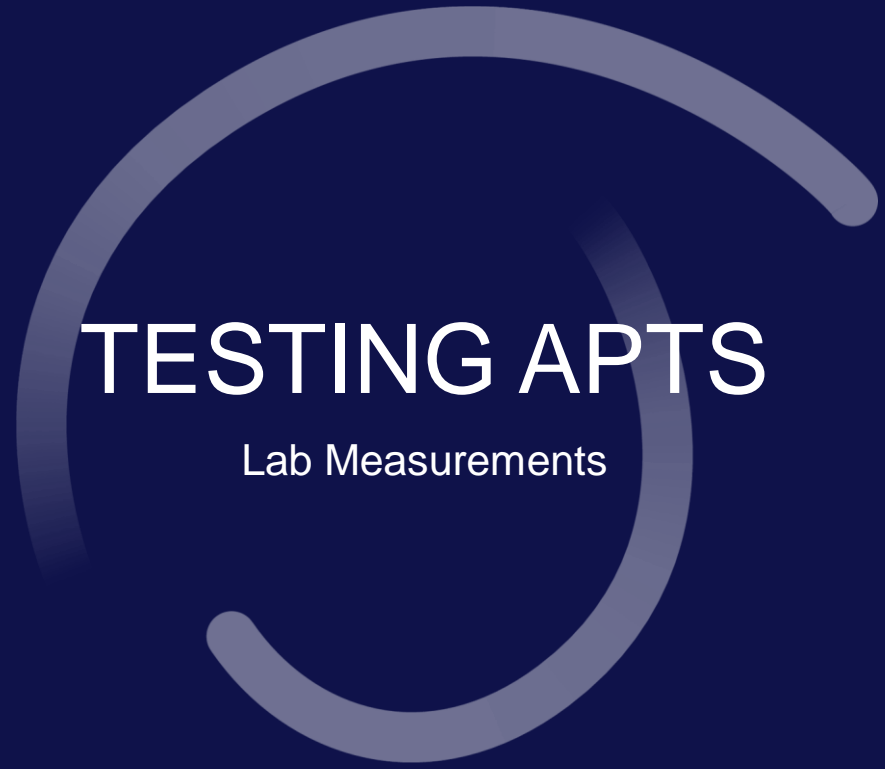
- **Reference**
- **Larger n-well collection electrode**
- **Finger-shaped p-well enclosure**
- **Smaller p-well enclosure**

P-Type: only reference variant on chip

Multiplexer: all four variants on same chip

Comparison of: pitches, variants and irradiation damage

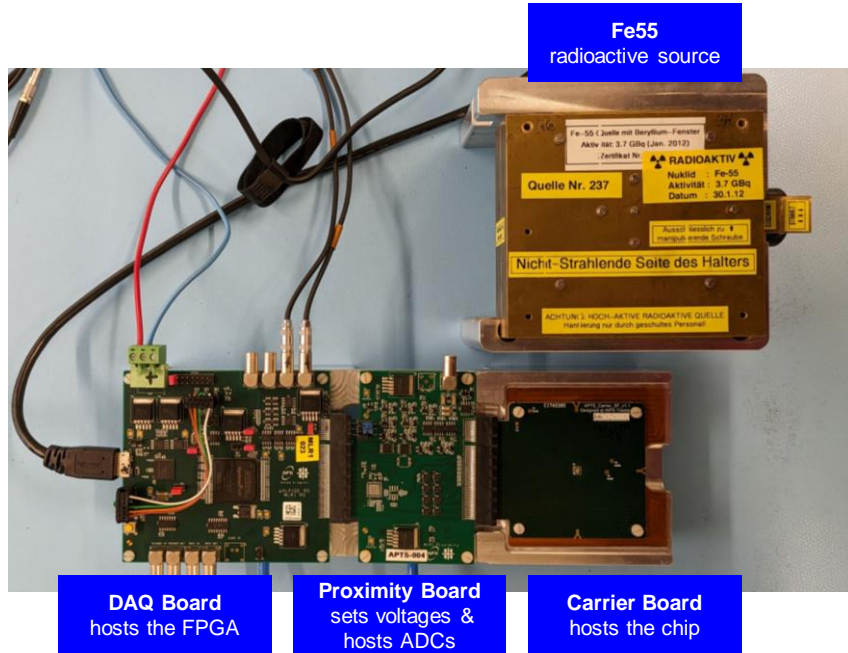




TESTING APTS

Lab Measurements

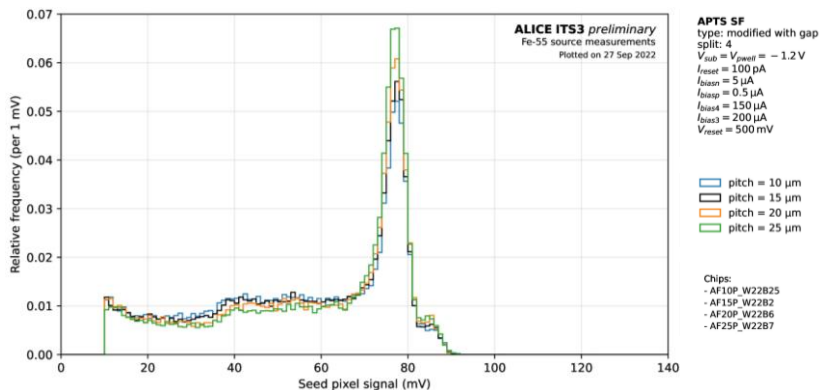
Lab Measurement Setup with Fe-55 Source



- Water cooling used to set a **standard temperature** during tests (16°-20°C)
- The measurement of the **Fe-55 spectrum** is used to **calibrate** the sensor readout to the collected charge at different **bias voltages**

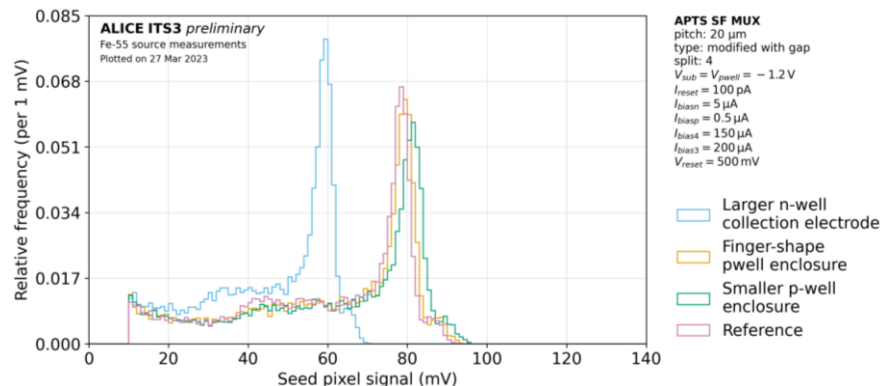
Charge Collection

Pitch Comparison



- The entire generated charge is collected pointing to the **near-full depletion** of the sensitive layer
- All pitches and variants show similar results indicating **efficient charge collection**
- Freedom to choose pitch depending on application

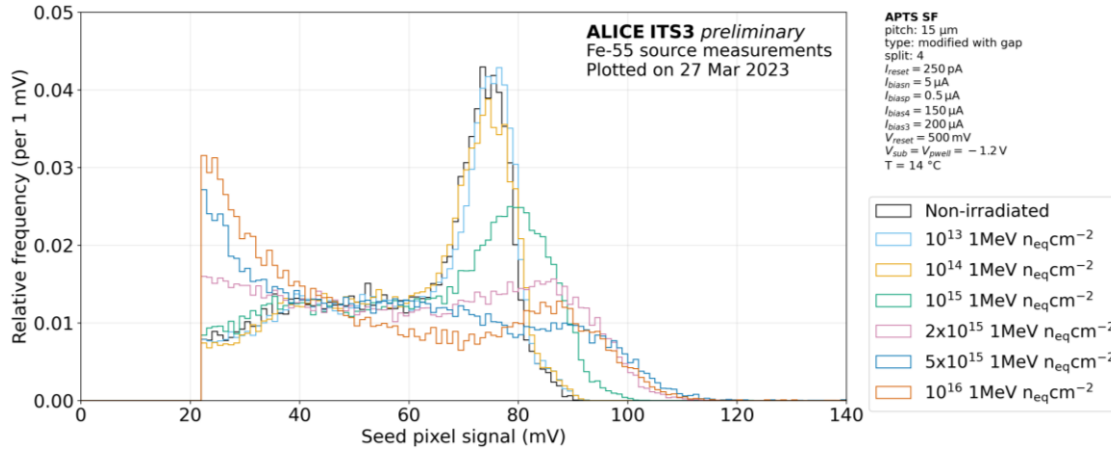
Variant Comparison



- Sensor variant with **higher capacitance** leads to **lower signal** in mV

Charge Collection

Irradiation Comparison

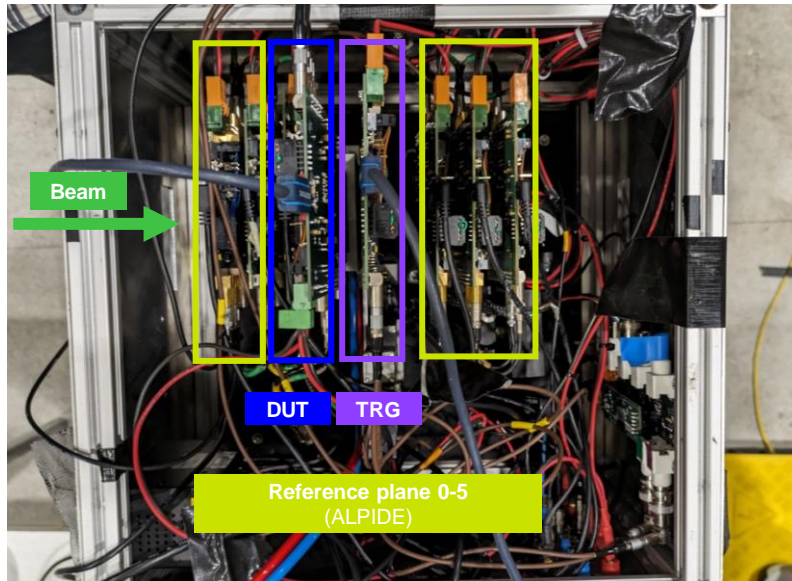


- Up to $10^{14} \text{ 1MeV } n_{\text{eq}}\text{cm}^{-2}$ all similar behaviour (ALICE ITS3 radiation tolerance requirement $< 10^{13}$ NIEL)
- After $10^{14} \text{ 1MeV } n_{\text{eq}}\text{cm}^{-2}$ performance worsens, less charge gets collected and Fe-55 peak becomes less visible

TESTING APTS

Test Beam Measurements

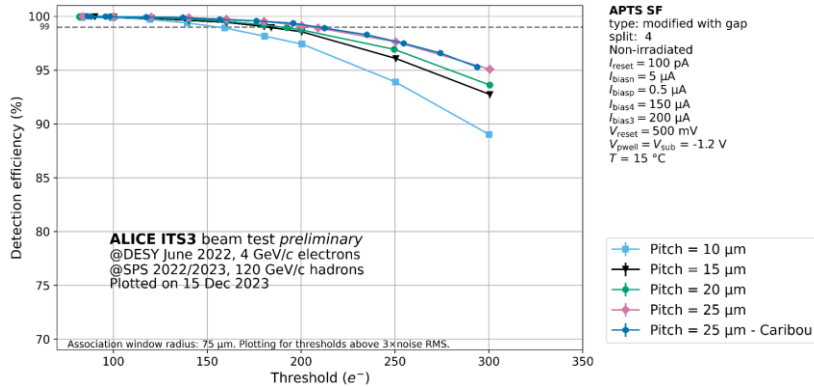
Test Beam Measurement Setup



- **6 ALPIDEs** (ITS2) as **reference planes** (not cooled)
- **1 APTS** sensor as **DUT** at standard temperature (~16°C)
- **1 APTS** as **trigger**
- Tested at
 - SPS with **120 GeV hadrons**
 - PS with **10 GeV hadrons**
 - DESY with **0.8-5 GeV electrons**
- The test beam measurements are used to determine the **detection efficiency** and the **spatial resolution**.
- All plots show points above 3 x RMS noise

Pitch Comparison

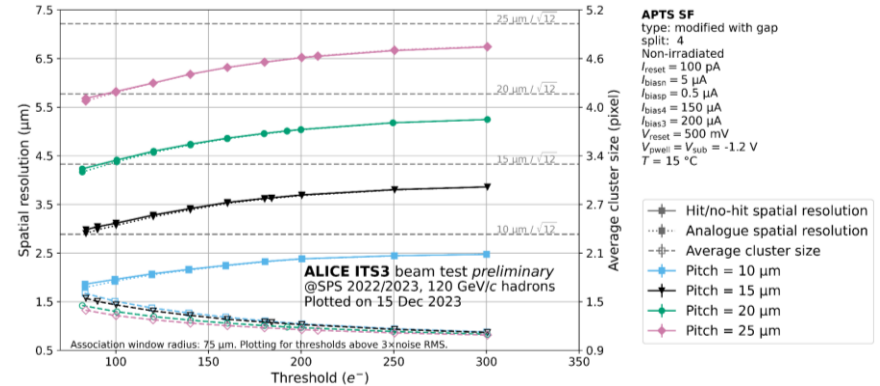
Detection Efficiency



99% efficiency reached for all pitches

- Worse efficiencies at higher thresholds due to more charge sharing
- Smaller pitches** \rightarrow **less range of operation** due to more charge sharing

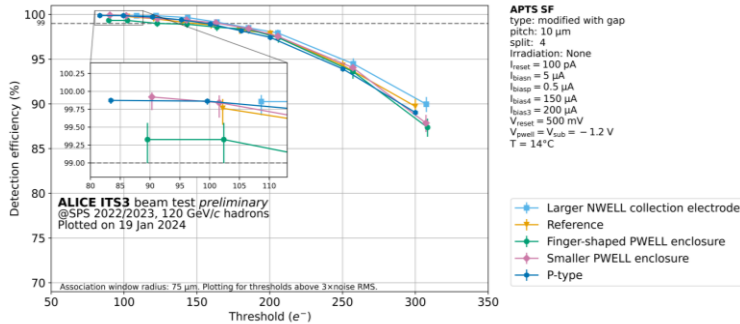
Spatial Resolution



- Spatial resolution better than $\text{pitch}/\sqrt{12}$ thanks to charge sharing
- 10 μm pitch sensor: extremely good resolution ($< 3 \text{ }\mu\text{m}$)

Variant Comparison

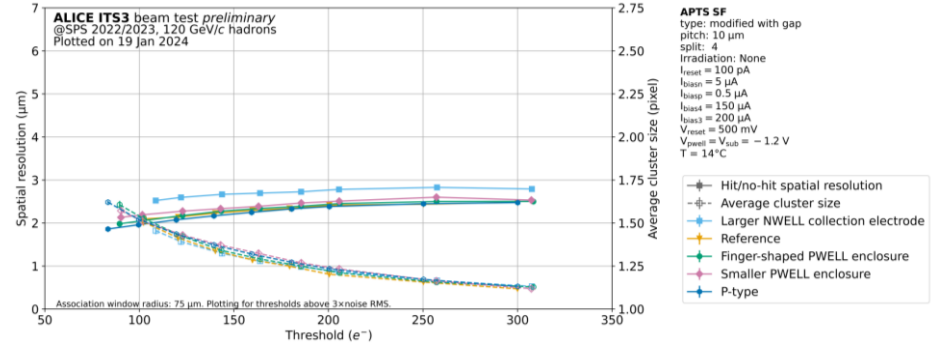
Detection Efficiency



99% efficiency reached for all variants

- RMS noise for multiplexer $\sim 13\text{-}14\%$ higher than P-type in all cases due to higher currents

Spatial Resolution

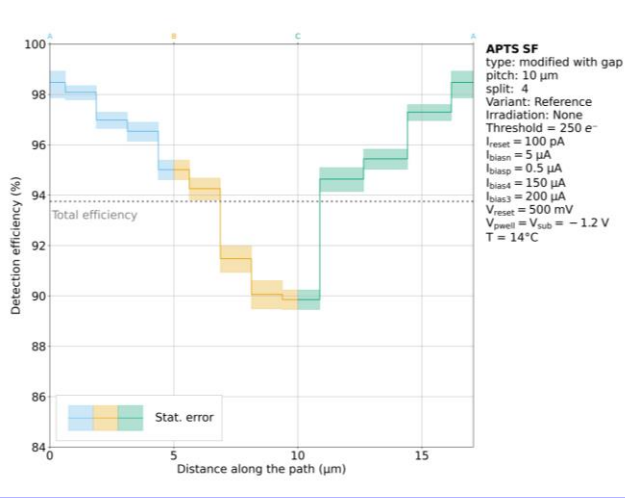
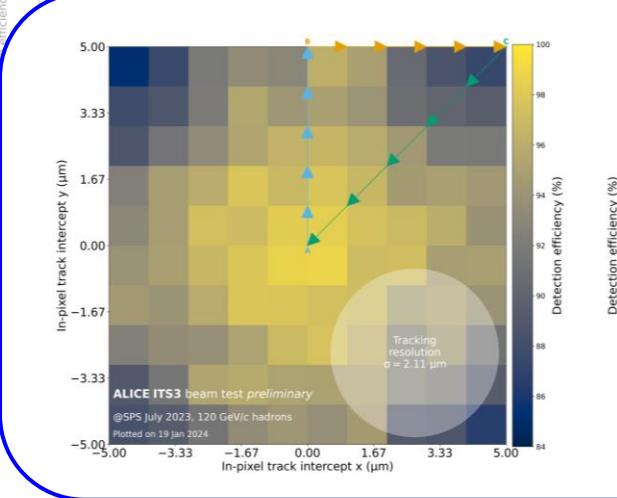
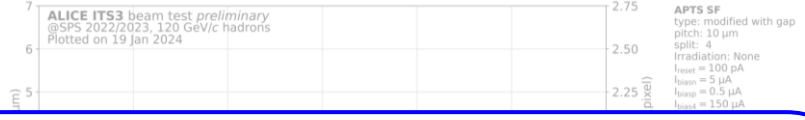
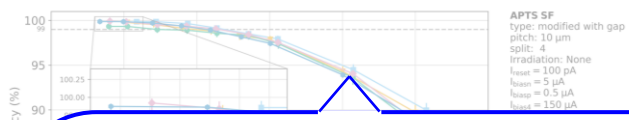


- More **charge sharing** improves the **spatial resolution**
- Little to no impact of sensor geometry except for large n-well variant

Variant Comparison

Detection Efficiency

Spatial Resolution



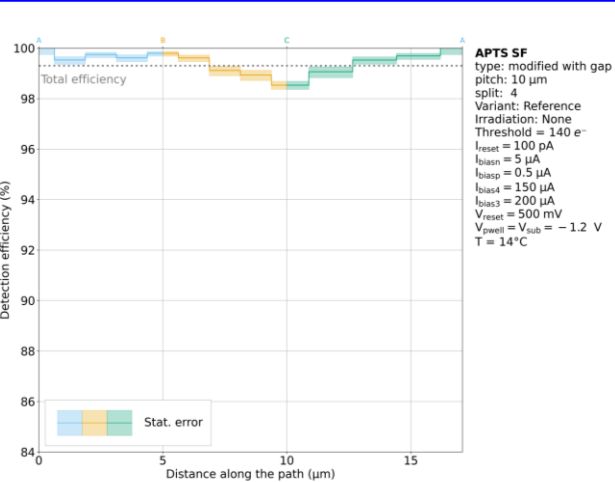
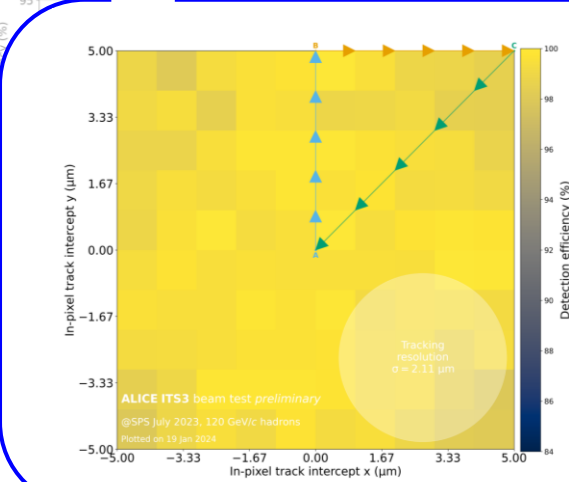
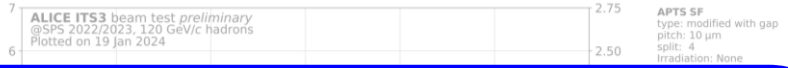
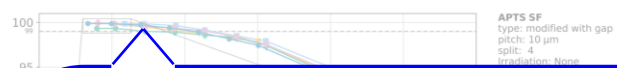
- Efficiency loss focused on the edges and corners of the pixel at high thresholds
- Little to no impact of sensor geometry variation

electrode pressure cell

Variant Comparison

Detection Efficiency

Spatial Resolution

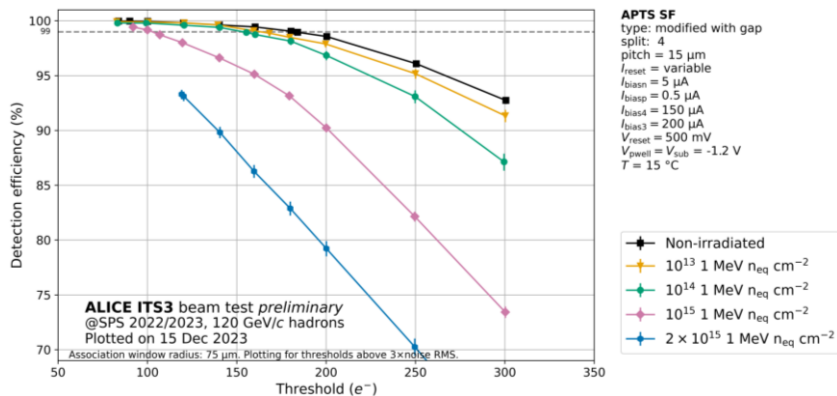


- Efficiency loss focused on the edges and corners of the pixel at high thresholds
- Little to no impact of sensor geometry variation

electrode
pressure
cell

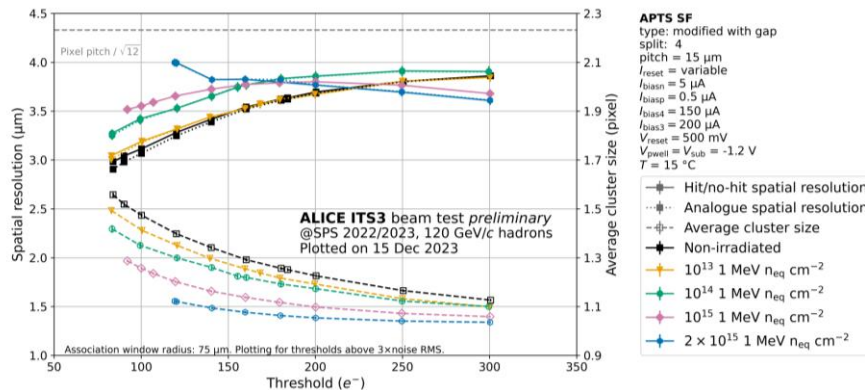
Irradiation Comparison

Detection Efficiency



99% efficiency reachable with irradiation **up to 10^{14} $1 \text{ MeV } n_{\text{eq}} \text{ cm}^{-2}$** with the application of bias voltage

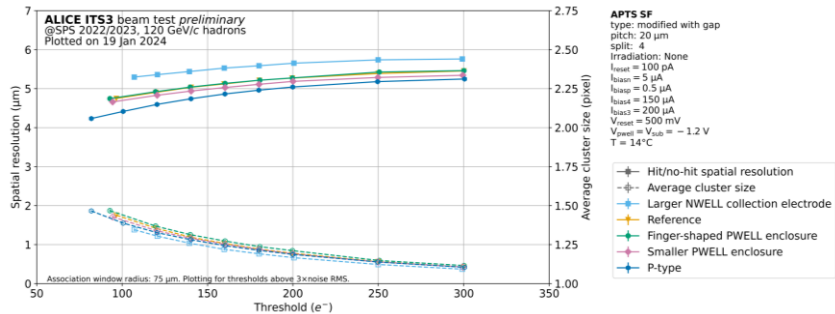
Spatial Resolution



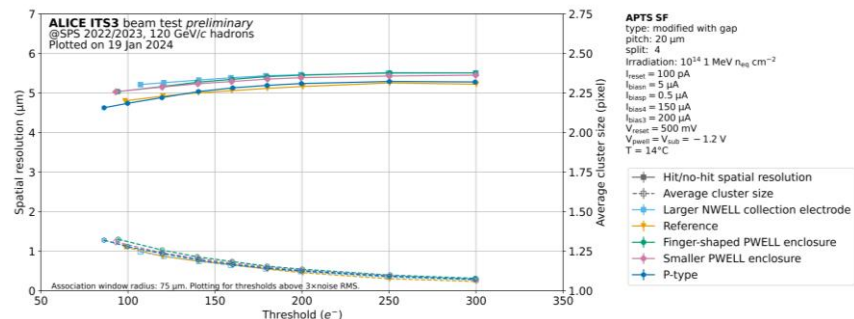
Resolution worsens after a irradiation of 10^{14} $1 \text{ MeV } n_{\text{eq}} \text{ cm}^{-2}$

Irradiation Comparison

Not Irradiated



Irradiation: $10^{14} \text{ 1MeV } n_{eq} \text{ cm}^{-2}$



Spatial resolution of **larger n-well less affected by irradiation** thanks to larger collection area but not surpassing performance of other sensor geometries



SUMMARY AND OUTLOOK

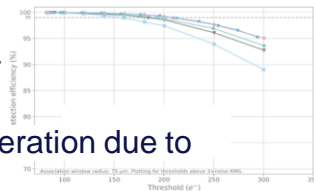
Summary and Outlook

Charge Collection:

- All pitches and variants very similar
- The entire generated charge is collected pointing to **near-full depletion** of sensitive layer

Efficiency:

- All pitches and variants very similar
- Over **99% efficiency** reached
- Smaller pitches → less range of operation due to charge sharing

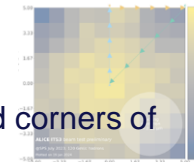


Resolution:

- Effect of charge sharing/cluster size visible
- 10 μm pitch sensor: extremely good resolution (<3 μm)

In-pixel study:

- Efficiency loss focused on the edges and corners of the pixel at high thresholds
- Little to no impact of sensor geometry variation



Radiation Tolerance:

- All variants very similar, good performance (operation over 99% efficiency) up to the irradiation level of 1e14 NIEL

APTS results show that sensor performance required by ITS3 detector design is feasible

- Testing of stitched design started
- Assembly of wafer-scale sensors defined
- TDR now with LHCC



Thank you
for your attention.



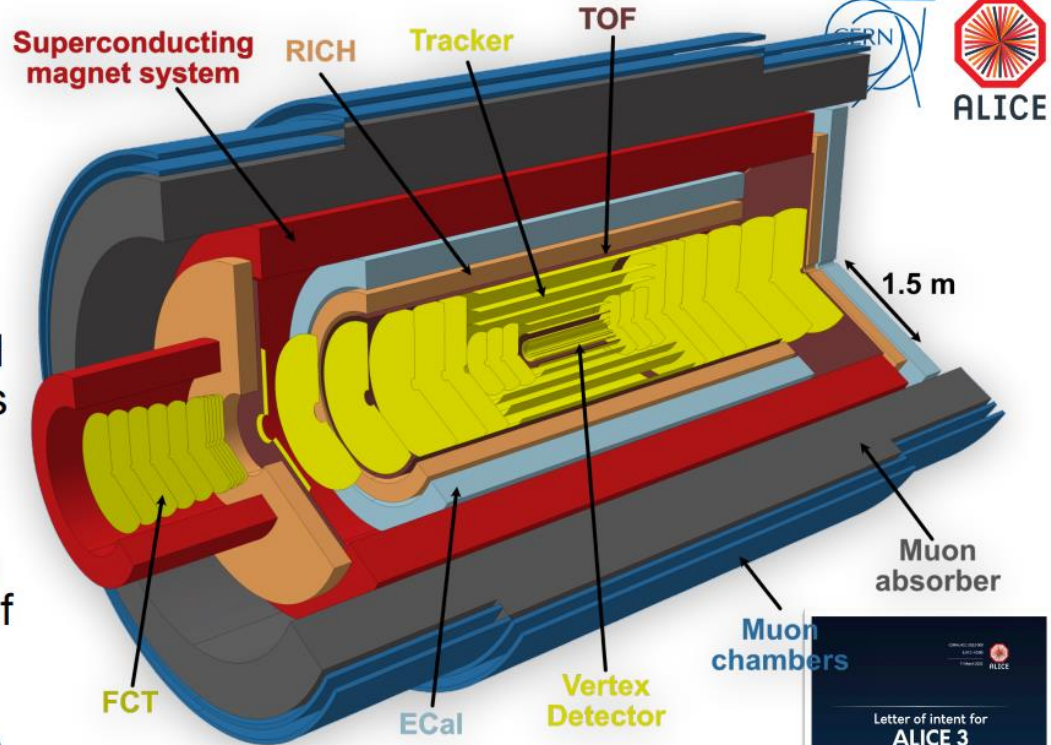
Back-up

ALICE 3

LHC LS4 2033/34

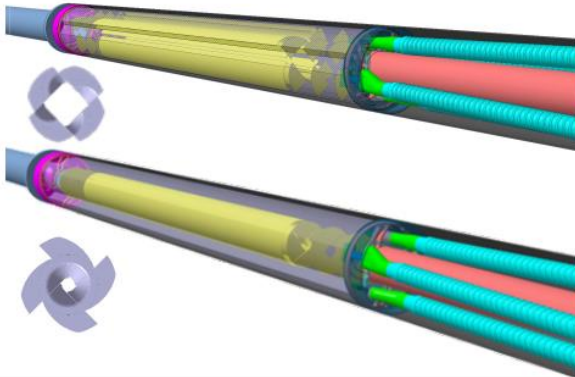
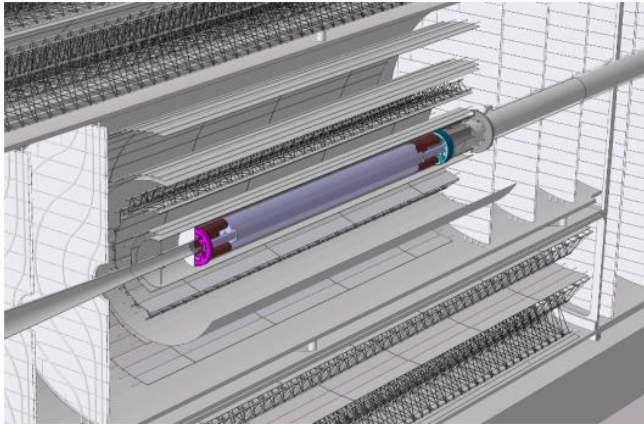
- ▶ ALICE 3 is centred around a 60 m² MAPS tracker
 - innermost layers will be based on wafer-scale Silicon sensors “iris tracker”, similar to ITS3 (but in vacuum)
 - outer tracker will be based on modules like ITS2 (but order of magnitude larger)

- ▶ *This is the next big and concrete step for this technology*



ALICE 3

vertex detector

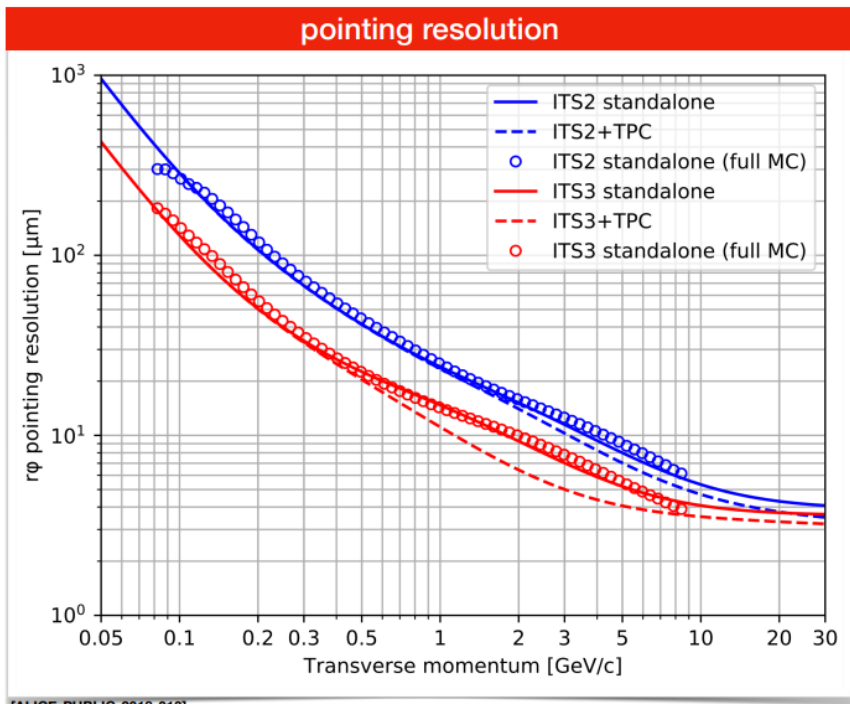


- ▶ Based on **wafer-scale, ultra-thin, curved MAPS**
 - radial distance from interaction point: **5 mm** (inside beampipe, retractable configuration)
 - unprecedented spatial resolution: $\approx 2.5 \mu\text{m}$
 - ... and material budget: $\approx 0.1\% X_0/\text{layer}$
 - at radiation levels of: $\approx 10^{16} \text{ 1MeV } n_{\text{eq}}/\text{cm}^2 + 300 \text{ Mrad}$
 - and hit rates up to: **94 MHz/cm²**

- ▶ Unprecedented performance figures
 - **largely leverages on the ITS3 developments**
 - pushes improvements on a number of fronts

ALICE ITS3

Performance improvement

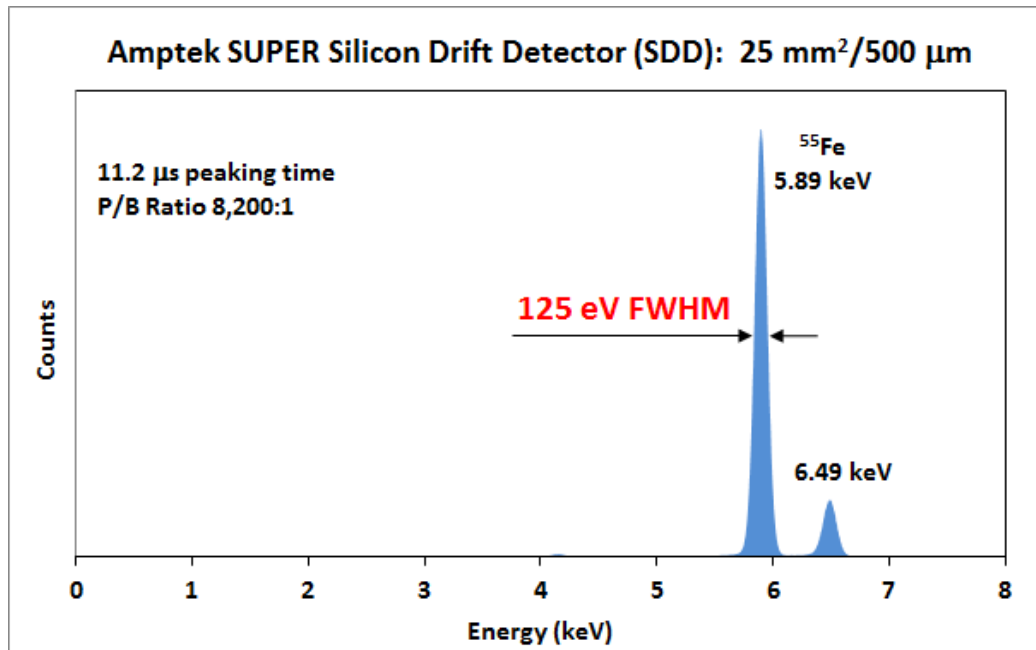


[ALICE-PUBLIC-2018-013]

improvement of factor 2 over all momenta

- ▶ Improvement of pointing resolution by:
 - drastic reduction of **material budget** (0.3 \rightarrow 0.05% X_0 /layer)
 - being **closer** to the interaction point (24 \rightarrow 18 mm)
 - thinner and smaller **beam pipe** (700 \rightarrow 500 μm ; 18 \rightarrow 16 mm)
- ▶ Directly boosts the ALICE core physics program that is largely based on:
 - low momenta
 - secondary vertex reconstruction
- ▶ E.g. Λ_c S/B improves by factor 10, significance by factor 4

Fe55 Spectrum



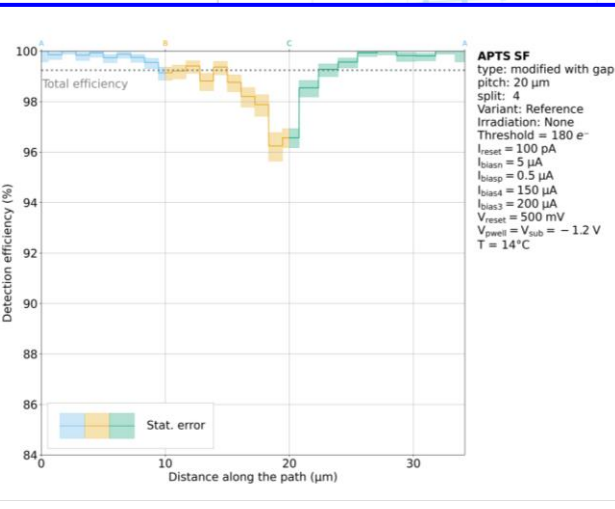
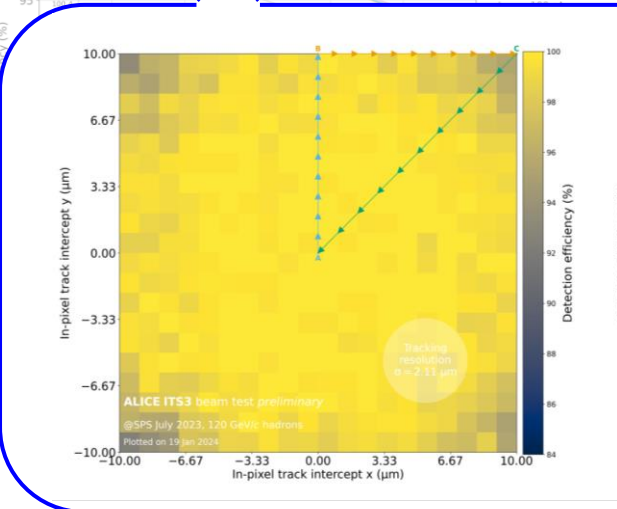
The measurement of the Fe55 spectrum is used to calibrate the sensor readout to the collected charge

- Number of electrons generated by K α : 1640
- Number of electrons generated by K β : 1800

Variant Comparison

Detection Efficiency

Spatial Resolution

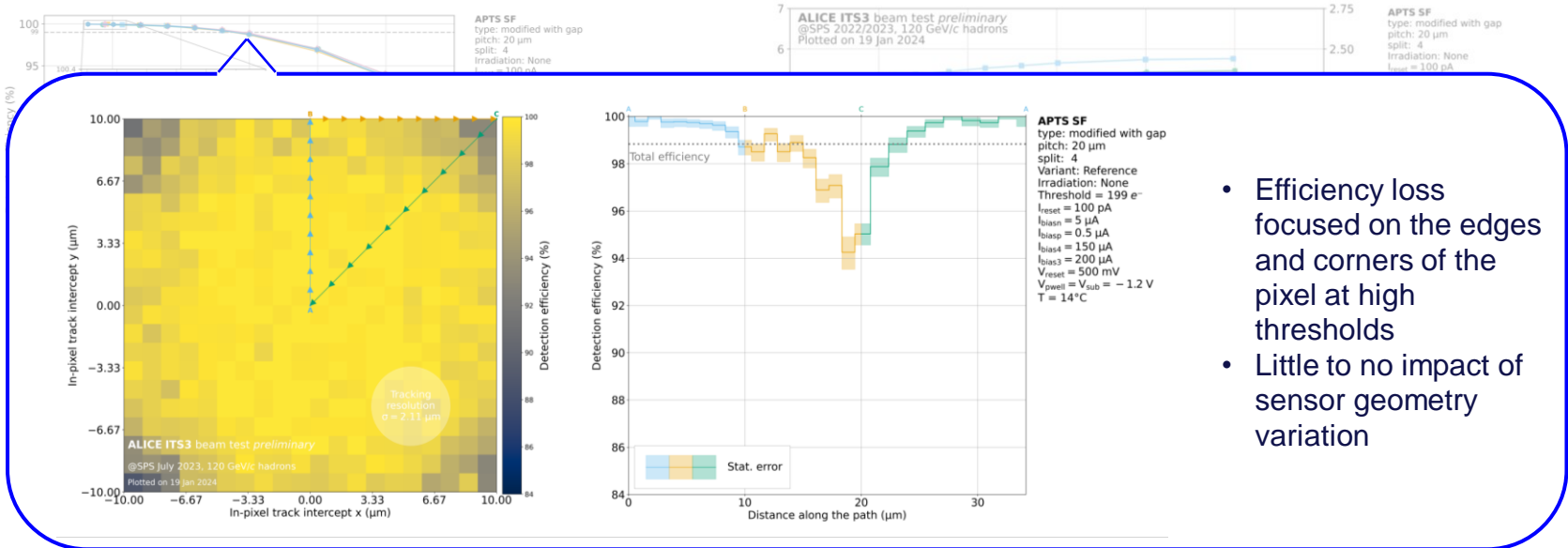


- Efficiency loss focused on the edges and corners of the pixel at high thresholds
- Little to no impact of sensor geometry variation

Variant Comparison

Detection Efficiency

Spatial Resolution



- Efficiency loss focused on the edges and corners of the pixel at high thresholds
- Little to no impact of sensor geometry variation